# The RF Line

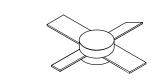
# **Microwave Pulse Power Transistors**

Designed for Class B and C common base amplifier applications in short and long pulse TACAN, IFF, DME, and radar transmitters.

- Guaranteed Performance @ 1090 MHz, 50 Vdc Output Power = 15 Watts Peak Minimum Gain = 10 dB
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Industry Standard Package
- Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input Matching for Broadband Operation

# **MRF1015MB**

15 W (PEAK), 960-1215 MHz MICROWAVE POWER **TRANSISTORS NPN SILICON** 



**CASE 332A-03, STYLE 1** 

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	VCES	60	Vdc	
Collector-Base Voltage	V <sub>СВО</sub>	60	Vdc	
Emitter-Base Voltage	V <sub>EBO</sub>	4.0	Vdc	
Collector Current — Continuous	IC	1.0	Adc	
Total Device Dissipation @ T <sub>C</sub> = 25°C (1) Derate above 25°C	P <sub>D</sub>	17.5 100	Watts mW/°C	
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C	

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	$R_{ heta JC}$	10	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS	OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, V <sub>BE</sub> = 0)	V(BR)CES	60		_	Vdc		
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>E</sub> = 0)	V(BR)CBO	60		_	Vdc		
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 1.0 mAdc, I <sub>C</sub> = 0)	V(BR)EBO	4.0	_	_	Vdc		
Collector Cutoff Current (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0)	ICBO	_	_	1.0	mAdc		
ON CHARACTERISTICS							

DC Current Gain	hFE	10	40	100	<b>—</b>
$(I_C = 250 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$					

NOTES:

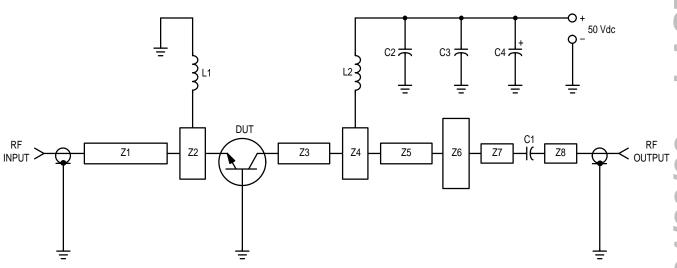
(continued)

- 1. These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.
- 2. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

MOTOROLA

## **ELECTRICAL CHARACTERISTICS** — **continued** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
DYNAMIC CHARACTERISTICS	DYNAMIC CHARACTERISTICS					
Output Capacitance (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	5.0	7.5	pF	
<b>FUNCTIONAL TESTS</b> (Pulse Width = 10 μs, Duty Cycle = 1.0%)	FUNCTIONAL TESTS (Pulse Width = 10 μs, Duty Cycle = 1.0%)					
Common-Base Amplifier Power Gain (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 15 W Peak, f = 1090 MHz)	G <sub>PB</sub>	10	12.5	_	dB	
Collector Efficiency (VCC = 50 Vdc, Pout = 15 W Peak, f = 1090 MHz)	η	30	35	_	%	
Load Mismatch (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 15 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Power Output				



C1, C2 — 220 pF 100 mil Chip Capacitor C3 — 0.1  $\mu$ F C4 — 47  $\mu$ F/75 V Electrolytic Capacitor L1, L2 — 3 Turns #18 AWG, 1/8" ID Z1–Z8 — Microstrip Board Material — 0.032" Glass Teflon  $\epsilon_\Gamma = 2.5$ 

Figure 1. 1090 MHz Test Circuit

### TYPICAL CHARACTERISTICS

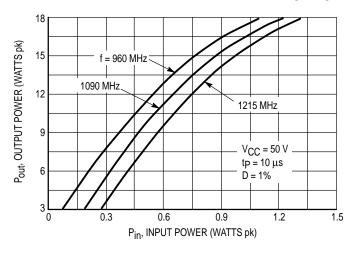


Figure 2. Output Power versus Input Power

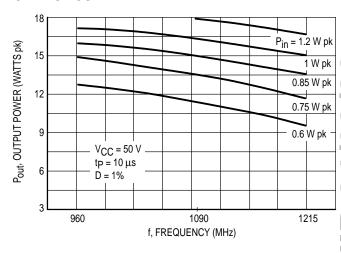


Figure 3. Output Power versus Frequency

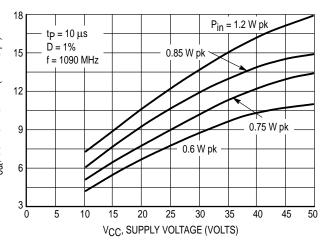


Figure 4. Output Power versus Supply Voltage

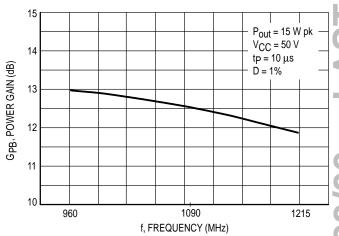
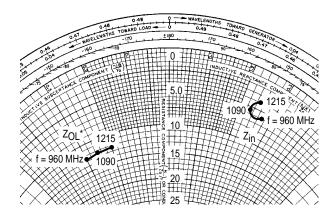


Figure 5. Power Gain versus Frequency

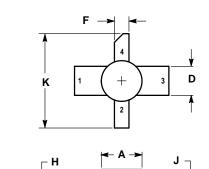


 $P_{out} = 15 \text{ W pk}$   $V_{CC} = 50 \text{ V}$  $t_p = 10 \text{ \mu s}$  D = 1%

f MHz	Z <sub>in</sub> Ohms	Z <sub>OL</sub> * Ohms
960	5.9 + j13.6	12.5 – j15
1090	5.5 + j11.5	12.4 – j12.8
1215	4.0 + j12.5	12.1 – i10

Z<sub>OL</sub>\* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage, and frequency.

Figure 6. Series Equivalent Input/Output Impedances



**CASE 332A-03 ISSUE D** 

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.270	0.290	6.86	7.36
С	0.115	0.135	2.93	3.42
D	0.195	0.205	4.96	5.20
F	0.095	0.105	2.42	2.66
Н	0.050	0.070	1.27	1.77
J	0.003	0.007	0.08	0.17
K	0.600		15.24	

- STYLE 1: PIN 1. BASE 2. EMITTER

  - 3. BASE 4. COLLECTOR

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USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado 80217. 1-303-675-2140 or 1-800-441-2447

JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 141, 4-32-1 Nishi-Gotanda, Shagawa-ku, Tokyo, Japan. 03-5487-8488

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